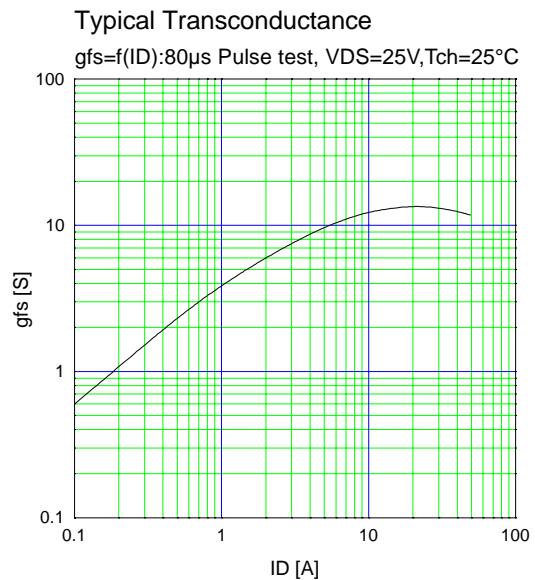
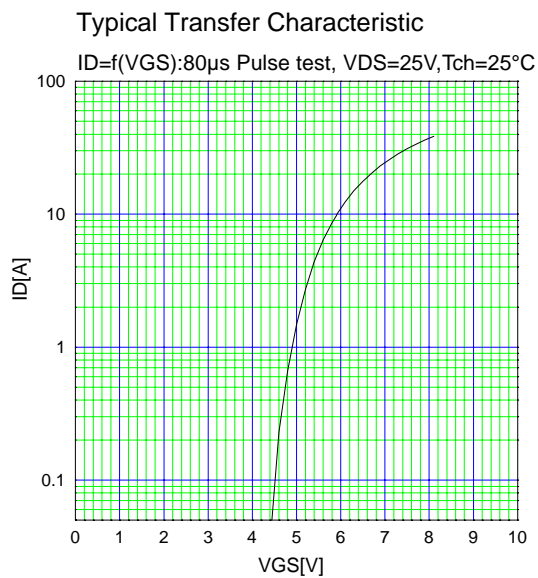
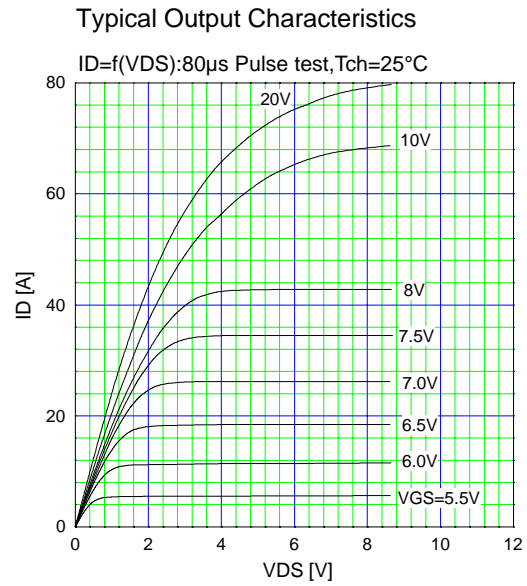
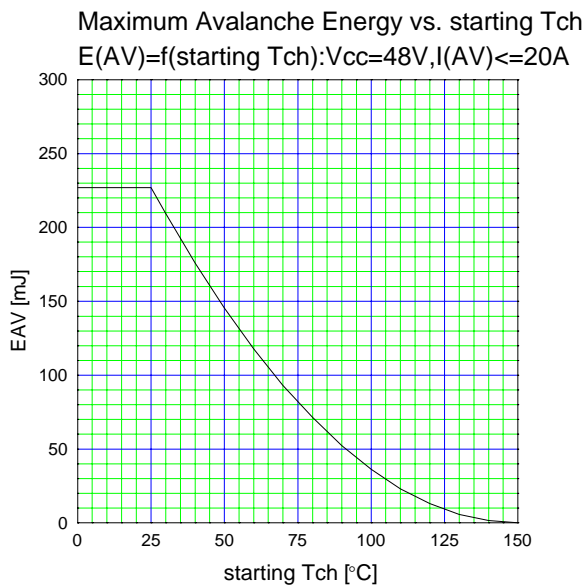
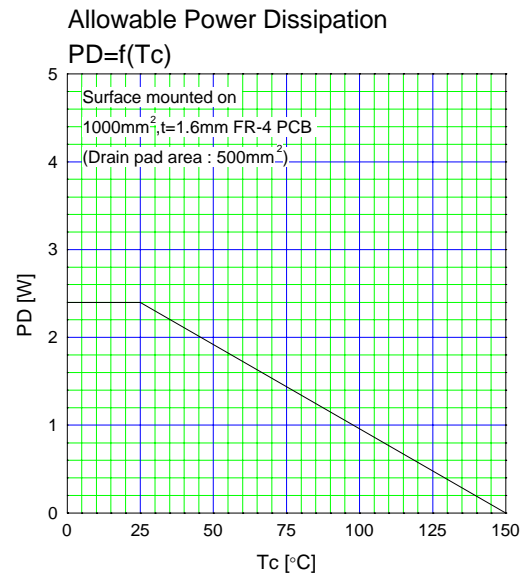
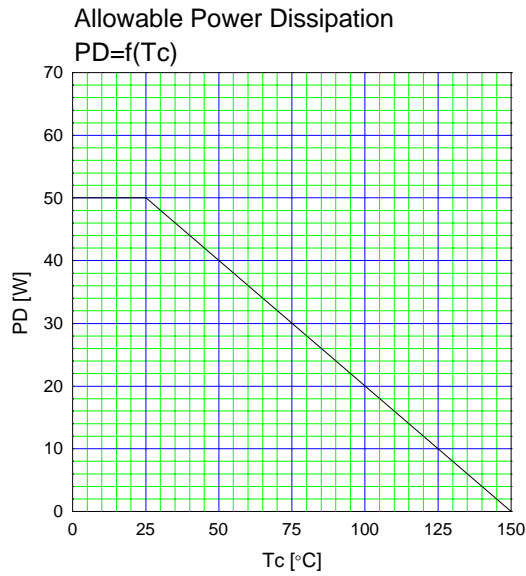
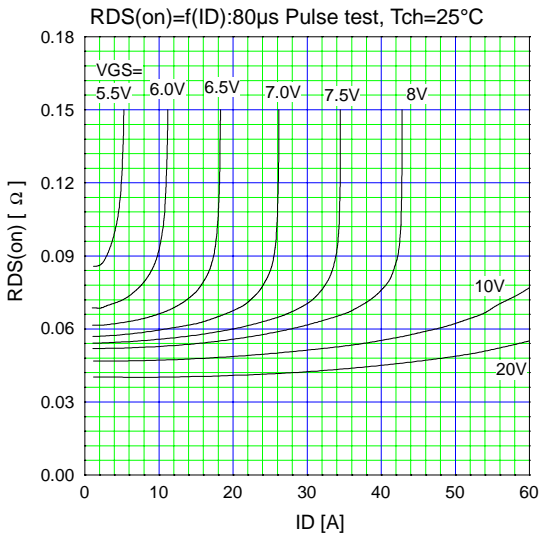


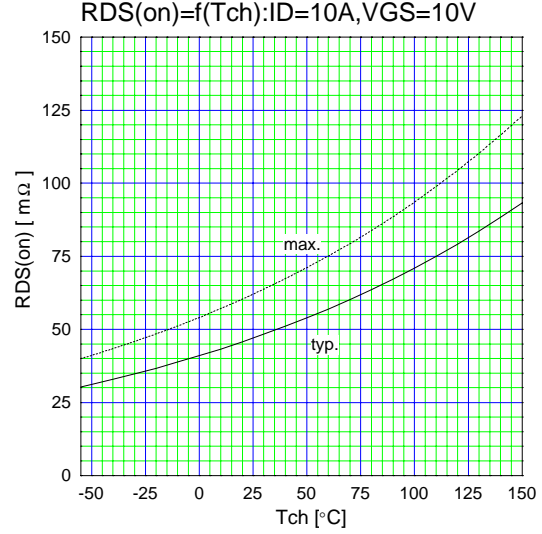
Characteristics



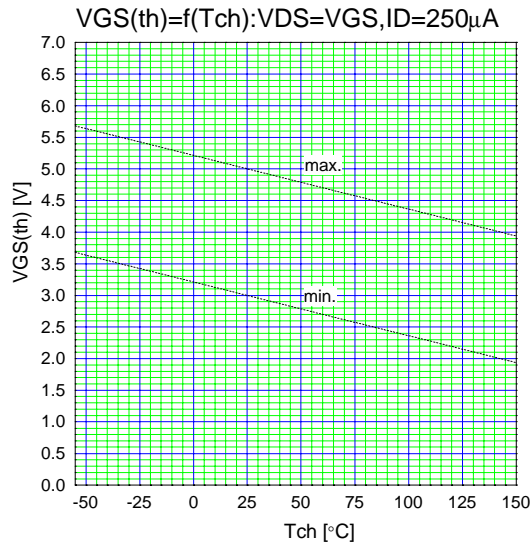
Typical Drain-Source on-state Resistance



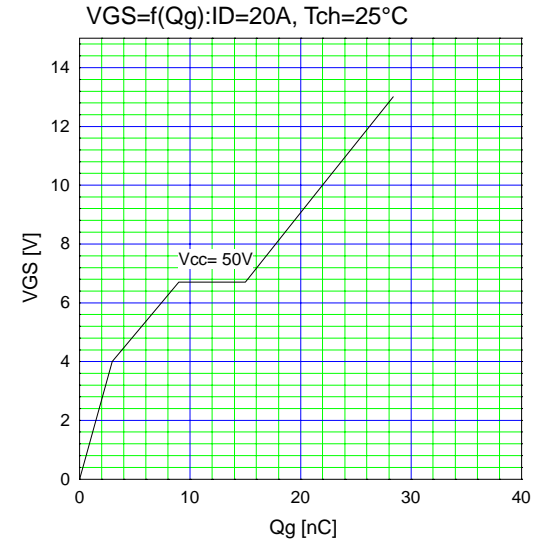
Drain-Source On-state Resistance



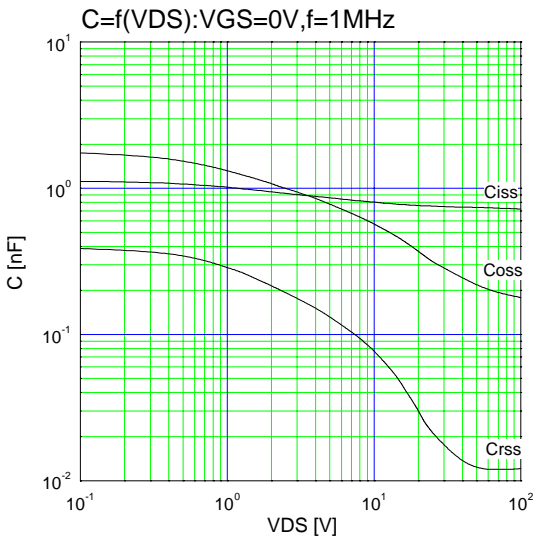
Gate Threshold Voltage vs. T_{ch}



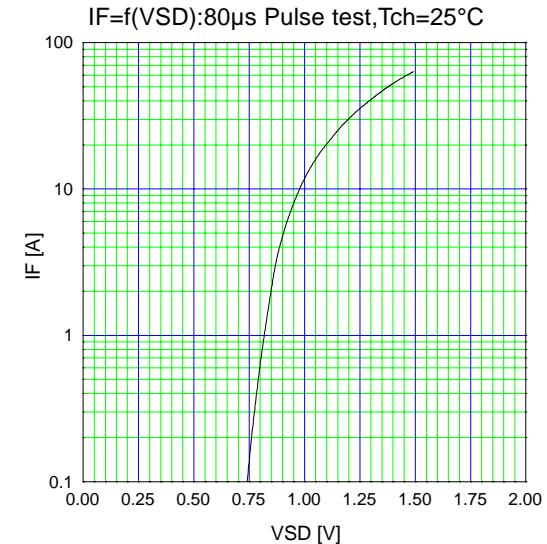
Typical Gate Charge Characteristics



Typical Capacitance

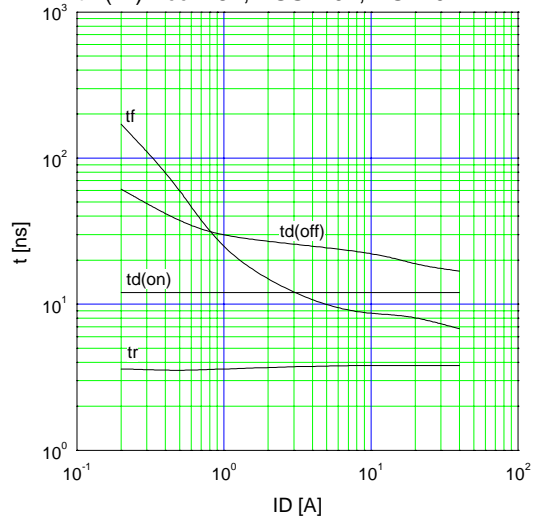


Typical Forward Characteristics of Reverse Diode



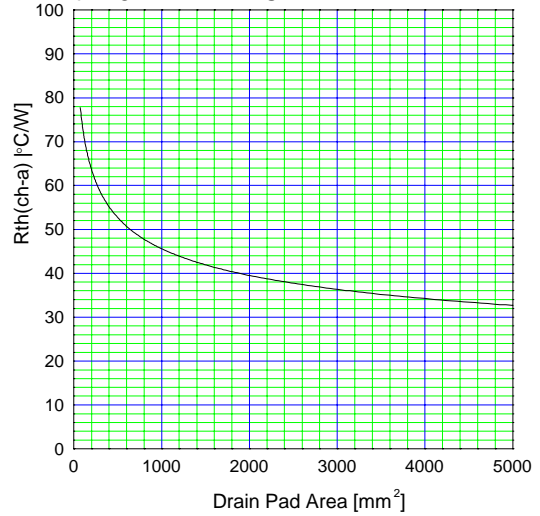
Typical Switching Characteristics vs. ID

$t=f(ID): V_{CC}=48V, V_{GS}=10V, R_G=10\Omega$



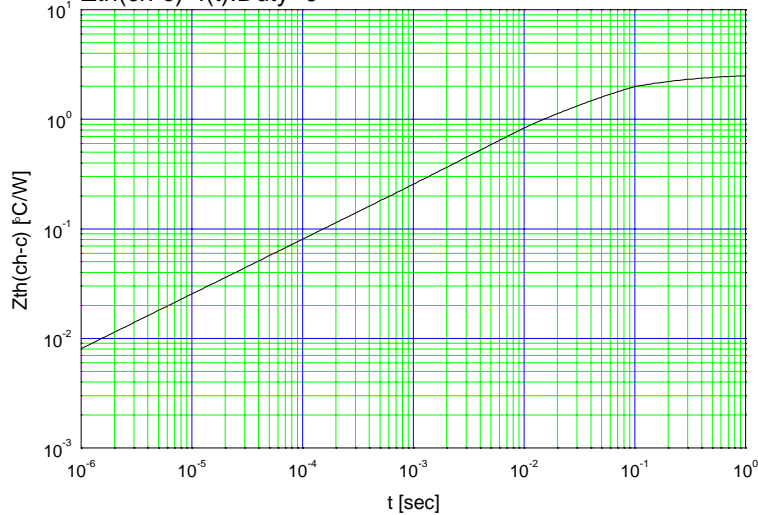
Thermal Resistance vs. Drain Pad area

$t=1.6mm$ FR-4 PCB



Transient Thermal Impedance

$Z_{th(ch-c)}=f(t): Duty=0$



Maximum Avalanche Current Pulsewidth

$I_{AV}=f(t_{AV}): starting T_{ch}=25^{\circ}C, V_{CC}=48V$

